ABSTRACT OF THE DISCLOSURE

A method for manufacturing a nitride semiconductor device in which nitride crystals are sequentially grown on a substrate such as sapphire by MOCVD or the like, and p electrode and n electrode are formed. The wafer is not cut along two perpendicular directions, but rather is cut along two directions that form a 120 degree angle, to obtain a rhombus shaped semiconductor chip. Because the wafer has a six-fold rotation symmetry, by cutting the wafer at an angle of 120 degrees, the cutting directions are equivalent and the wafer can be cut in directions along which it can be easily split.